INCH-POUND MIL-M-38510/314C <u>14 July 2003</u> SUPERSEDING MIL-M-38510/314B 23 May 1978

## MILITARY SPECIFICATION

## MICROCIRCUITS, DIGITAL, LOW-POWER SCHOTTKY, TTL, MONOSTABLE MULTIVIBRATORS, MONOLITHIC SILICON

#### Inactive for new design after 18 April 1997.

#### This specification is approved for use by all Departments and Agencies of the Department of Defense.

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1. SCOPE

1.1 <u>Scope.</u> This specification covers the detail requirements for monolithic silicon, low-power Schottky TTL, monostable multivibrator microcircuits. Two product assurance classes and a choice of case outlines and lead finishes are provided for each type and are reflected in the complete part number. For this product, the requirements of MIL-M-38510 have been superseded by MIL-PRF-38535, (see 6.3).

1.2 Part number. The part number should be in accordance with MIL-PRF-38535, and as specified herein.

1.2.1 <u>Device types.</u> The device types should be as follows:

Device type	<u>Circuit</u>
01	Dual monostable multivibrator, retriggerable, with clear
02	Dual monostable multivibrator, Schmitt trigger inputs, with clear
03	Single monostable multivibrator, retriggerable, with clear

1.2.2 Device class. The device class should be the product assurance level as defined in MIL-PRF-38535.

1.2.3 Case outlines. The case outlines should be as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	<b>Terminals</b>	Package style
А	GDFP5-F14 or CDFP6-F14	14	Flat pack
В	GDFP4-14	14	Flat pack
С	GDIP1-T14 or CDIP2-T14	14	Dual-in-line
D	GDFP1-F14 or CDFP2-F14	14	Flat pack
E	GDIP1-T16 or CDIP2-T16	16	Dual-in-line
F	GDFP2-F16 or CDFP3-F16	16	Flat pack
2	CQCC1-N20	20	Square leadless chip carrier

Beneficial comments (recommendations, additions, deletions) and any pertinent data which may be of use in improving this document should be addressed to: Commander, Defense Supply Center Columbus, ATTN: DSCC-VAS, P. O. Box 3990, Columbus, OH 43216-5000, by using the self addressed Standardization Document Improvement Proposal (DD Form 1426) appearing at the end of this document or by letter.

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# 1.3 Absolute maximum ratings.

Supply voltage range Input voltage range	-1.5 V dc at -18 mA to 5.5 V dc
Storage temperature range	-65° to +150°C
Maximum power dissipation per flip-flop, (P <sub>D</sub> ) <u>1</u> /	
Device type 01	110 mW dc
Device type 02	149 mW dc
Device type 03	61 mW dc
Lead temperature (soldering, 10 seconds)	300°C
Thermal resistance, junction to case $(\theta_{JC})$ :	
Cases A, B, C, D, E, F, and 2	(See MIL-STD-1835)
Junction temperature (T <sub>J</sub> ) <u>2</u> /	175°C

# www.DataSheet4U.com 1.4 <u>Recommended operating conditions.</u>

Supply voltage (V <sub>CC</sub> )	4.5 V dc minimum to 5.5 V dc maximum
Minimum high level input voltage (V <sub>IH</sub> )	
Maximum low level input voltage (VIL)	0.7 V dc
Case operating temperature range (T <sub>c</sub> )	-55° to +125°C
Minimum pulse width	
Input pulse rise/fall time, device type 02	
Schmitt, B input	1 V/s minimum
Logic, A input	
Clear-inactive-state setup time	
Device type 02	15 ns minimum
External timing resistance, Rext	
Device type 01, 03	5 kΩ minimum, 180 kΩ maximum
Device type 02	
External timing capacitance, Cext	
Device type 01, 03	No restriction
Device type 02	1,000 μF maximum
Output duty cycle, device type 02	
$R_T = 2 k\Omega$	50% duty cycle maximum
$T_T$ = 70 k $\Omega$	90 % duty cycle maximum
Wiring capacitance, Rext/Cext terminal	
Device type 01, 03 (referenced to GND)	50 pF maximum

 $<sup>\</sup>frac{1}{2}$  Must withstand the added P<sub>D</sub> due to short-circuit test (e.g., I<sub>OS</sub>).  $\frac{2}{2}$  Maximum junction temperature shall not be exceeded except for allowable short duration burn-in screening conditions in accordance with MIL-PRF-38535.

#### 2. APPLICABLE DOCUMENTS

#### 2.1 Government documents.

2.1.1 <u>Specifications and Standards.</u> The following specifications and standards form a part of this specification to the extent specified herein. Unless otherwise specified, the issues of these documents shall be those listed in the issue of the Departments of Defense Index of Specifications and Standards (DODISS) and supplement thereto, cited in the solicitation.

#### **SPECIFICATION**

#### DEPARTMENT OF DEFENSE

MIL-PRF-38535 - Integrated Circuits (Microcircuits) Manufacturing, General Specification for.

#### STANDARDS

## DEPARTMENT OF DEFENSE

MIL-STD-883	-	Test Method Standard for Microelectronics.
MIL-STD-1835	-	Interface Standard Electronic Component Case Outlines

(Unless otherwise indicated, copies of the above specifications and standards are available from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.2 <u>Order of precedence.</u> In the event of a conflict between the text of this specification and the references cited herein, the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

#### 3. REQUIREMENTS

3.1 <u>Qualification</u>. Microcircuits furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturers list before contract award (see 4.3 and 6.4).

3.2 <u>Item requirements</u>. The individual item requirements shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein.

3.3 <u>Design, construction, and physical dimensions.</u> The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein.

3.3.1 <u>Terminal connections and logic diagrams.</u> The terminal connections and logic diagrams shall be as specified on figure 1.

3.3.2 Truth table and functional description. The truth table and functional description shall be as specified on figure 2.

3.3.3 <u>Schematic circuits</u>. The schematic circuits shall be maintained by the manufacturer and made available to the qualifying activity and the preparing activity upon request.

3.3.4 Case outlines. The case outlines shall be as specified in 1.2.3.

3.4 Lead material and finish. The lead material and finish shall be in accordance with MIL-PRF-38535 (see 6.6).

3.5 <u>Electrical performance characteristics</u>. The electrical performance characteristics are as specified in table I, and apply over the full recommended case operating temperature range, unless otherwise specified.

3.6 <u>Electrical test requirements.</u> The electrical test requirements for each device class shall be the subgroups specified in table II. The electrical tests for each subgroup are described in table III.

3.7 Marking. Marking shall be in accordance with MIL-PRF-38535.

3.8 <u>Microcircuit group assignment</u>. The devices covered by this specification shall be in microcircuit group number 10 (see MIL-PRF-38535, appendix A).

4. VERIFICATION

4.1 <u>Sampling and inspection</u>. Sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not effect the form, fit, or function as described herein.

4.2 <u>Screening</u>. Screening shall be in accordance with, MIL-PRF-38535 and shall be conducted on all devices prior to qualification and quality conformance inspection. The following additional criteria shall apply:

- a. The burn-in test duration, test condition, and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document control by the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015 of MIL-STD-883.
- b. Interim and final electrical test parameters shall be as specified in table II, except interim electrical parameters test prior to burn-in is optional at the discretion of the manufacturer.
- c. Additional screening for space level product shall be as specified in MIL-PRF-38535, appendix B.

4.3 <u>Qualification inspection</u>. Qualification inspection shall be in accordance with MIL-PRF-38535.

4.4 <u>Technology Conformance Inspection (TCI)</u>. Technology conformance inspection shall be in accordance with MIL-PRF-38535 and herein for groups A, B, C, and D inspections (see 4.4.1 through 4.4.4).

4.4.1 Group A inspection. Group A inspection shall be in accordance with table III of MIL-PRF-38535 and as follows:

- a. Tests shall be as specified in table II herein.
- b. Subgroups 4, 5, and 6 shall be omitted.

# TABLE I. Electrical performance characteristics.

Test	Symbol	Conditions	Device	Lin	nits	Unit
		$-55^{\circ}C \le T_{C} \le +125^{\circ}C$	types	Min	Max	
		unless otherwise specified				
High level output voltage	V <sub>OH</sub>	$V_{CC} = 4.5 \text{ V}, \text{ V}_{IL} = 0.7 \text{ V},$	All	2.5		V
		$V_{IH} = 2.0 \text{ V}, I_{OH} = -400 \mu\text{A}$				
Low level output voltage	V <sub>OL</sub>	$V_{CC} = 4.5 \text{ V}, \text{ V}_{IL} = 0.7 \text{ V},$	All		0.4	V
		V <sub>IH</sub> = 2.0 V, I <sub>OL</sub> = 4 mA				
Input clamp voltage	VIC	$V_{CC} = 4.5 \text{ V}, \text{ I}_{IN} = -18 \text{ mA},$	All		-1.5	V
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Low level input current	I <sub>IL1</sub>	$V_{CC} = 5.5 \text{ V}, \text{ V}_{IN} = 0.4 \text{ V}$	01, 03	-160	-400	μA
	1.	-				
Low level input current	I <sub>IL2</sub>		02	-30	-680	
at clear input	_		02	20	400	
Low level input current at A <sub>IN</sub>			02	-30	-400	
Low level input current B <sub>IN</sub>			02	-30	-580	
High level input current	I <sub>IH1</sub>	$V_{CC} = 5.5 \text{ V}, V_{IN} = 2.7 \text{ V}$	All		20	μA
High level input current	I <sub>IH2</sub>	$V_{CC} = 5.5 \text{ V}, \text{ V}_{IN} = 5.5 \text{ V}$	All		100	
Short circuit output current	los	$V_{CC} = 5.5 \text{ V}, \text{ V}_{IH} = 5.5 \text{ V},$	All	-15	-130	mA
		V <sub>IL</sub> = GND				
Supply current (quiescent)	I <sub>CC1</sub>	$V_{CC} = 5.5 V$	02		11	mA
		4				
Supply current (quiescent or	I <sub>CC2</sub>		01		20	
triggered)		-	03		11	
Supply current (triggered)	I <sub>CC3</sub>		02		27	
Propagation delay time low to	t <sub>PLH1</sub>	V <sub>CC</sub> = 5.0 V	01, 03	5	57	ns
high level from input A		$C_L = 50 \text{ pF} \pm 5\%, R_L = 2 \text{ k}\Omega \pm 5\%$	02	5	113	]
Propagation delay time low to	t <sub>PLH2</sub>	Cext = 1/	01, 03	5	74	
high level from input B		Rext = 1/2	02	5	90	1
Propagation delay time low to	t <sub>PLH3</sub>	] _	01, 03	5	75	]
high level from clear	-		02	5	105	]
Propagation delay time	t <sub>PHL1</sub>	]	01, 03	5	75	
high to low level from input A			02	5	128	

See footnotes at end of table.

	Test	Symbol	Conditions	Device	Lin	nits	Unit
			$-55^{\circ}C \le T_C \le +125^{\circ}C$	types	Min	Max	
			unless otherwise specified				
Pr	ropagation delay time	t <sub>PHL2</sub>	$V_{CC} = 5.0 V$	01, 03	5	92	ns
r	high to low level from input B		$C_L = 50 \text{ pF} \pm 10\%$	02	5	105	
			$R_L = 2k\Omega \pm 5\%$				
Pr	ropagation delay time	t <sub>PHL3</sub>	Cext = <u>1</u> /	01, 03	5	48	ns
ł	nigh to low level from clear		Rext = <u>1</u> /	02	5	90	
Mi	inimum pulse width	t <sub>P(MIN)</sub>	$V_{CC} = 5.0 V$	01, 03		308	ns
c	of Q output		$C_L = 50 \text{ pF} \pm 10\%$				
W	idth of Q output pulse	t <sub>P1</sub>	$R_L = 2k\Omega \pm 5\%$	02	20	91	
		t <sub>P2</sub>	Cext = <u>2</u> / ±10%	02	70	195	
		t <sub>P3</sub>	Rext = <u>2</u> / ±10%	02	600	850	
		t <sub>P4</sub>		01, 03	3.0	6.25	μs
		t <sub>P5</sub>		02	5.5	8.5	ms

# TABLE I. <u>Electrical performance characteristics</u> - Continued.

1/ For propagation delay tests, see table III for Cext and Rext values.

 $\underline{2}$ / t<sub>P(MIN)</sub> test, Cext = open and Rext = 5 k $\Omega$ .

 $t_{P1}$  test, Cext = open and Rext = 2 k $\Omega$ .

 $t_{P2}$  test, Cext = 80 pF and Rext = 2 k $\Omega$ .

 $t_{\text{P3}}$  test, Cext = 100 pF and Rext = 10 k $\Omega.$ 

 $t_{P4}$  test, Cext = 1,000 pF and Rext = 10 k $\Omega$ .

 $t_{P5}$  test, Cext = 1µF and Rext = 10 k $\Omega$ .

	Subgroups	(see table III)
MIL-PRF-38535	Class S	Class B
test requirements	devices	devices
Interim electrical parameters	1	1
Final electrical test parameters	1*, 2, 3, 7, 9, 10, 11	1*, 2, 3, 7, 9
Group A test requirements	1, 2, 3, 7, 8, 9, 10, 11	1, 2, 3, 7, 8, 9
Group B electrical test parameters when using method 5005 QCI option	1, 2, 3 9, 10, 11	N/A
Group C end-point electrical parameters	1, 2, 3, 9, 10, 11	1, 2, 3
Additional electrical subgroups for group C inspections	N/A	10, 11
Group D end-point electrical parameters	1, 2, 3	1, 2, 3

## TABLE II. Electrical test requirements.

\*PDA applies to subgroup 1.

4.4.2 Group B inspection. Group B inspection shall be in accordance with table II MIL-PRF-38535.

4.4.3 Group C inspection. Group C inspection shall be in accordance with table IV of MIL-PRF-38535 and as follows:

- a. End-point electrical parameters shall be as specified in table II herein.
- b. The steady-state life test duration, test condition, and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document control by the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.
- c. Subgroups 3 and 4 shall be added to group C inspection parameters for class B devices and shall consist of the tests, conditions, and limits specified for subgroups 10 and 11 of group A.

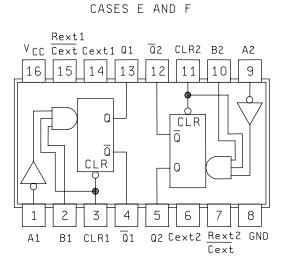
4.4.4 <u>Group D inspection</u>. Group D inspection shall be in accordance with table V of MIL-PRF-38535. End-point electrical parameters shall be as specified in table II herein.

4.5 <u>Methods of inspection</u>. Methods of inspection shall be specified and as follows:

4.5.1 <u>Voltage and current.</u> All voltages given are referenced to the microcircuit ground terminal. Currents given are conventional and positive when flowing into the referenced terminal.

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DEVICE TYPE 01

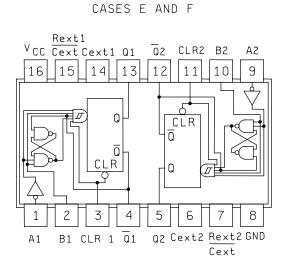


CASE 2 Cext2 Q2 NC Q1 CLR1 8 7 5 4 6 Rext2 Cext 3 B1 9 GND 10 2 A1 NC 11 1 NC A2 12 20 V<sub>CC</sub>  $19 \frac{\text{Rext}1}{\text{Cext}}$ B2 13 15 16 17 18 14 CLR2 Q2 NC Q1 Cext1

FIGURE 1. Terminal connections.

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DEVICE TYPE 02



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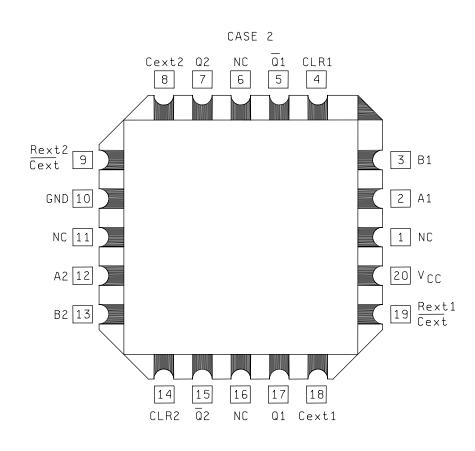
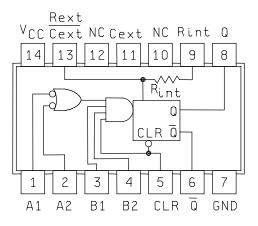


FIGURE 1. <u>Terminal connections</u> - Continued.





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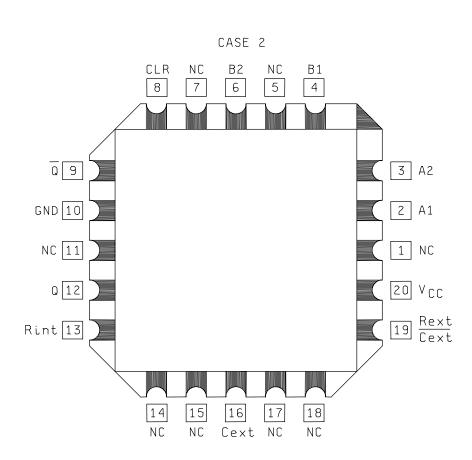


FIGURE 1. Terminal connections - Continued.

# Device type 01 and 02

	NPUTS		OUT	PUTS
CLEAR	А	В	Q	$\overline{Q}$
L	Х	Х	L	Н
Х	н	Х	L	Н
Х	Х	L	L	Н
н	L	$\uparrow$		Ц
н	$\downarrow$	Н		
<b>↑</b>	L	Н		Ц

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## Device type 03

		INPUTS			OUT	PUTS
CLEAR	A1	A2	B1	B2	Q	IQ
L	Х	Х	Х	Х	L	Н
Х	Н	Н	Х	Х	L	Н
Х	Х	Х	L	Х	L	Н
Х	Х	Х	Х	L	L	Н
Н	L	Х	$\uparrow$	Н	Г	IJ
н	L	Х	Н	$\uparrow$	Г	
Н	Х	L	$\uparrow$	Н	Г	
Н	Х	L	Н	$\uparrow$	Π	Ц
Н	Н	$\downarrow$	Н	Н	Г	
Н	$\downarrow$	$\downarrow$	Н	Н	Γ	Ц
Н	$\downarrow$	Н	Н	Н	Π	Ц
$\uparrow$	L	Х	Н	Н	Γ	
$\uparrow$	Х	L	Н	Н	Г	Ц

NOTES:

- 1. H = high level (steady state), L = low level (steady state),  $\uparrow$  = transition from low to high level,
  - $\downarrow$  = transition from high to low level,  $\square$  = one high level pulse,  $\square$  = one low level pulse,
  - X = irrelevant (any input, including transitions).
- 2. To use the internal timing resistor of device type 03 connect Rint to  $V_{CC}$ .
- 3. An external timing capacitor may be connected between Cext and Rext/Cext (positive).
- 4. For accurate repeatable pulse widths, connect an external resistor between Rext/Cext and V<sub>CC</sub> with Rint open circuited.
- 5. To obtain variable pulse widths, connect external variable resistance between Rint or Rext/Cext and V<sub>CC</sub>.

FIGURE 2. Truth table and functional description.

## Device types 01 and 03

This multivibrator features d-c triggering from gated low level active (A inputs), and high level active (B inputs). Output pulse width is a function of external capacitor and resistor values. Retriggering of input before output terminates, extends output pulse width. Overriding clear feature permits termination of output pulse width at a predetermined time independent of R and C timing components.

RETRIGGER PULSE SEE NOTE B INPUT -tp+tpLH -OUTPUT Q OUTPUT WITHOUT t ρ RETRIGGER OUTPUT PULSE CONTROL USING RETRIGGER PULSE B INPUT CLEAR OUTPUT WITHOUT CLEAR OUTPUT Q OUTPUT PULSE CONTROL USING CLEAR INPUT

NOTE:

Retrigger pulse must not start before 0.22 Cext (in picofarads) nanoseconds after previous trigger pulse.

FIGURE 2. Truth table and functional description - Continued.

## Device type 01 and 03 (Continued)

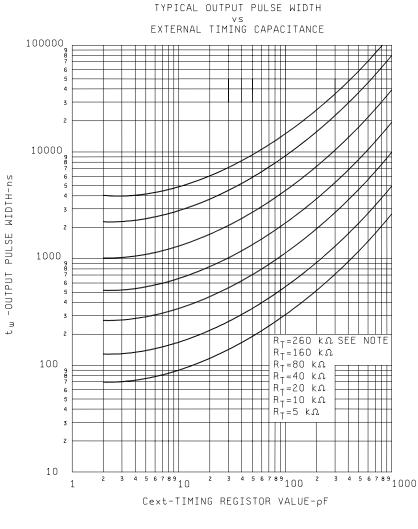
The output pulse width (tp) is a function of the external capacitor and resistor values.

For output pulse widths when Cext > 1,000 pF, tp is defined as :

tp  $\approx 0.4 R_T Cext$  Where  $R_T$  is in k $\Omega$ , Cext is in pF, and tp is in ns.

For output pulse widths when Cext < 1,000 pF, tp is defined as:

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NOTE:

This value of resistance exceeds the maximum recommended for use over the full temperature range

FIGURE 2. Truth table and functional description - Continued.

## Device type 02

This multivibrator features a negative transition triggered input and a positive transition triggered input, either of which can be used as an inhibit input. Pulse triggering occurs at a particular voltage level, not directly related to transition time of input pulse. Once fired, the outputs are independent of further transitions of A and B inputs, and are a function of the timing components. Output pulses can be terminated by the overriding clear, independent of R and C timing components.

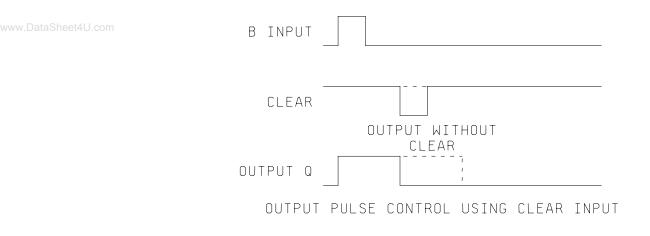


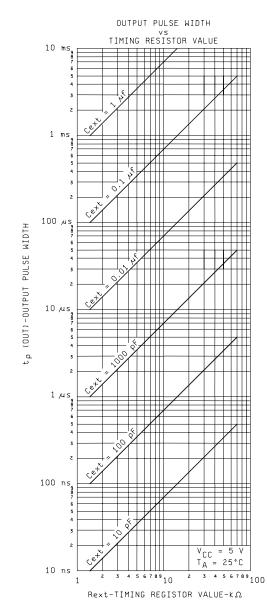
FIGURE 2. <u>Truth table and functional description</u> - Continued.

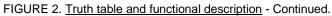
# Device type 02 (Continued)

The output pulse width (tp) is a function of the external capacitor and resistor values.

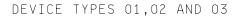
The output pulse width is defined as :

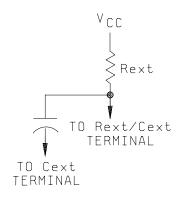
tp  $\,\approx\,$  0.7 R\_T Cext  $\,$  Where R\_T is in k\Omega, Cext is in pF, and tp is in ns.





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# TIMING COMPONENT CONNECTIONS

FIGURE 2. Truth table and functional description - Continued.

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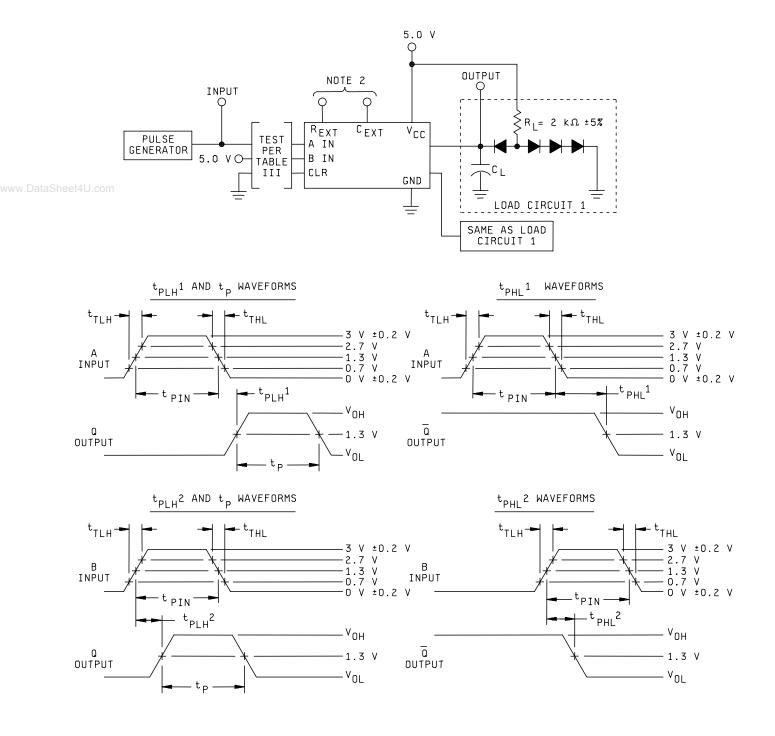
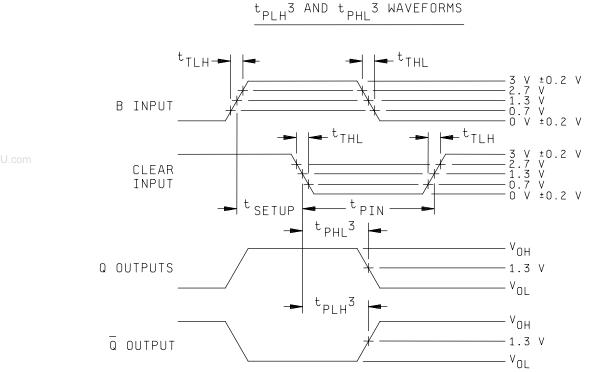


FIGURE 3. Switching test circuit and waveforms for device types 01 and 03.



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## NOTES:

- 1. Pulse generator has the following characteristics: PRR  $\leq$  1.0 MHz, t<sub>PIN</sub>  $\geq$  40 ns, t<sub>THL</sub>  $\leq$  6 ns, t<sub>TLH</sub>  $\leq$  15 ns, and Z<sub>OUT</sub> = 50 $\Omega$ .
- 2. See table III notes for Rext, Cext values.
- 3.  $C_L = 50 \text{ pF} \pm 10\%$  including scope probe, wiring and stray capacitance, without package in test fixture.
- 4. All diodes are 1N3064, or 1N916 or equivalent.
- 5. Load circuit on a given output is only required where the specified test in table III indicates "OUT" on that output.
- 6.  $t_{SETUP}$  (max) shall be  $\leq$  50% of the typical output pulse width for the actual Cext used (see figure 2).

FIGURE 3. Switching test circuit and waveforms for device types 01 and 03 - Continued.

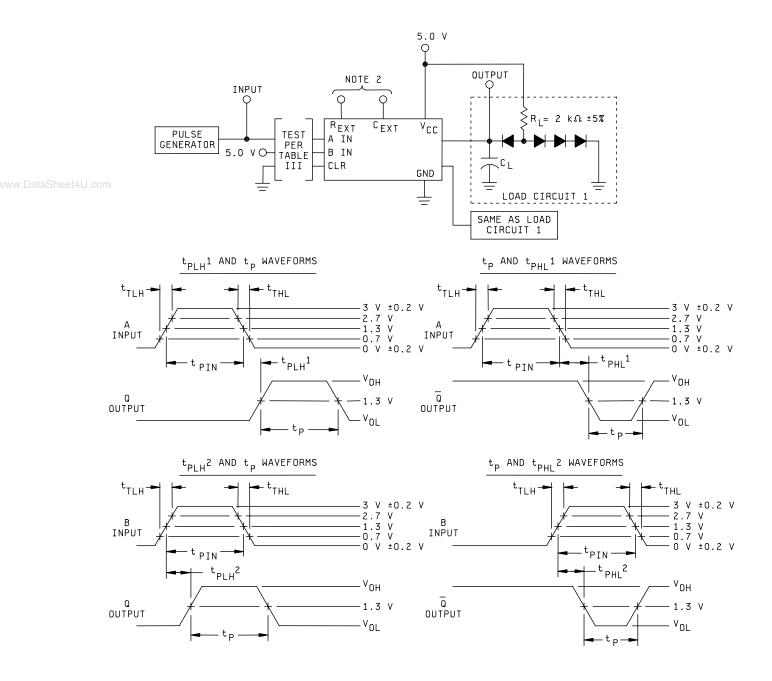
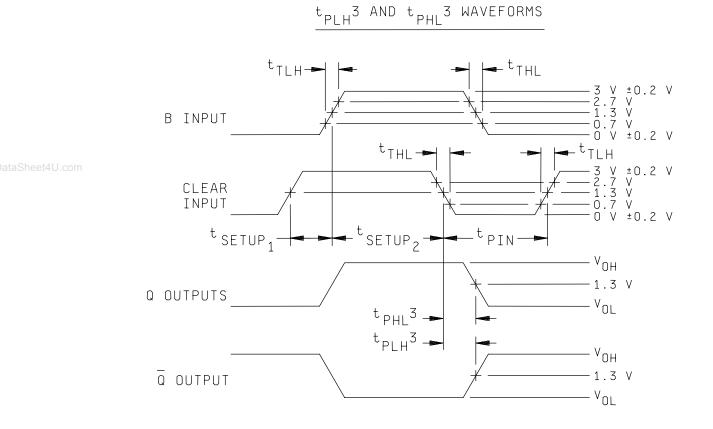


FIGURE 4. Switching test circuit and waveforms for device type 02.



NOTES:

- 1. Pulse generator has the following characteristics: PRR  $\leq$  1.0 MHz, t<sub>PIN</sub>  $\geq$  40 ns, t<sub>TLL</sub>  $\leq$  6 ns, t<sub>TLH</sub>  $\leq$  15 ns, t<sub>SETUP1</sub> (CLEAR INACTIVE) = 15 ns and Z<sub>OUT</sub> = 50 $\Omega$ .
- 2. See table III notes for Rext, Cext values.
- 3.  $C_{L} = 50 \text{ pF} \pm 10\%$  including scope probe, wiring and stray capacitance, without package in test fixture.
- 4. All diodes are 1N3064, or 1N916 or equivalent.
- 5. Load circuit on a given output is only required where the specified test in table III indicates "OUT" on that output.
- 6.  $t_{SETUP}$  (max) shall be  $\leq$  50% of the typical output pulse width for the actual Cext used (see figure 2).

FIGURE 4. Switching test circuit and waveforms for device type 02 - Continued.

		Unit		>	=			=	-	-	-		-	-	=	-	-	ЧЧ			=	=	=	=	-		-	=	=	-	-	-	-	МА	=	-	-		-	=	-	-	]
		its	Max					0.4	-	-	-	-1.5	=	-		-	=	-400		=	=	=	20	=	-		=	100	8 =	-	-		=	-100	-130	-100	-130	4	-100	-130	-100	-130	-
		Limits	Min	2.5		-	-										007	-160		=	=	=												-15	-30	-15	-30		-15	-30	-15	-30	
		Measured terminal		'ā	Q1	_ Q2	Q2	۵1 م	'n	Q2	_ 02	A1	B1	CLR1	A2	B2	CLR2	A1	5 13		AZ R2	CLR2	A1	B1	CLR1	A2 B2		A1	B1	CLR1	A2	B2	CLR2	'n,	a'	a1	Q1		ā2	ā2	Q2	Q2	
16		20	V <sub>cc</sub>	4.5 V	=	-	-	=	-	=	-	=	-	=	-	-	= [	5.5 V		=	=	-	-	=	-		=	-	-	-	=	-	-	-	-	-			-	-	-	-	
15		19	Rext1		GND				GND																											GND	GND						
14		18	Cext1																																								
13	1	17	Ø		4 mA			4 mA																		T			Ī	Ī						GND	GND						
	1	15	ā2			4 mA					4 mA																		ľ									1	GND	GND			
11		14	CLR2			2.0 V	2.0 V			2.0 V	2.0 V						-18 mA					0.4 V					~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~	2.1 V					5.5 V				l	1	GND	GND	4.5 V	4.5 V	
10			B2			0.7 V	2.0 V			0.7 V						-18 mA					041					1/ 2 0	× 1.7					5.5 V						1	GND	GND	4.5 V	4.5 V	
6	,	12	A2			2.0 <	о			2.0 V					-18 mA	1				~~~~	_				:	2.7 V					5.5 V									GND	с 0	с U	
8	,	10	GND	GND	-	=	-	=	-	=	-	-	-	-	-	-				=	-	-	-	-	-		=	-	-	-	=	-	-		-	-	-		-	-			
7			Rext2				GND				GND																														GND	GND	
9			Cext2 F				-				-																															-	
5	,		Q2 (				4 mA			H MA																															GND	GND	
4		5	ā1	4 mA			4		4 mA	4																			T					GND	GND							0	
3		4	CLR1	2.0 V	2.0 V				2.0 V 4					-18 mA						0.4 <					2.7 V				T	5.5 V				GND	GND	4.5 V	4.5 V						
2	1			0.7 V 2	2.0 V 2				2.0 V 2				-18 mA						0.4 V					2.7 V	2				5.5 V	-				GND	GND (	4.5 V 4	4.5 V 4						
-		5		2.0 V 0	C 2		-	>	5 C			-18 mA	-					0.4 V	2		+		2.7 V			╉	+	55V	+					GND	GND	C 4	C 4						
ses	E, F	Case 2	Test no.	1 2	2	e			9	7	8	9 -18		11	12	3			16	10	ο σ	0			0	24 25	0.0			6	0	1					КТ КТ		Ко	CKT	к К	, Kt	
Cai					- 1								-	-	-	-						- 10			2	. 1 0	N C	10		10	e	ς,			33 (	34 CKT	34 (		35 ( Å	35 (	36 ( ∆	390	_
		ol STD-883 method -		3006	-	•	•	3007	-	•	-							3009		= 2	-	-	3010				-	=	•	-	•	•		3011	=	=	•		-	-	•	-	
		up Symbol		V <sub>OH</sub>	ပ္ဂ			VoL				2	2				-	<u> </u>	2 cee	lion			Ē					of the	ZHI					_o									
		Subgroup		-	Tc = 25°C																																						

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TABLE III. Group A inspection for device type 01.

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		Unit		тA	ШA																			us.			=	=	=	-	-	-	-	=			=
		S	Max	20	20			See notes	A, B, D,		-						-		-	-	-	-		38	38	49	50	-	-	-	61	61	32	32	205		-
		Limits	Min					0,																ç.				-	-	-	-	-	-				
		Measured terminal		Vcc	V <sub>cc</sub>			AI	outputs "	-	=				-	-	-	-	-	=	-	-		A1 to Q1	A2 to Q2	B2 to Q2		CLR2 to 02	A2 to G2	A1 to 01	B1 to _01	B2 to G2	CLR2 to Q2	CLR1 to Q1	01	<u></u> 6	02 02
	ω		8				-	_	ō												_	_	-	_	A	, B	5 6	CLR	A2	A1	B1	B2	CLF	CLF	$\left  \right $	_	_
	16	20	1 V <sub>cc</sub>	5.5	5.5 V		1	5.0 V		-	-	-		-	-	-	-	-	-	-	-	-		2 O.G			-	-	-	-	-	-	-	-			-
et4U.	:0m	19	Rext1					LL -		-	-	-			-	-	-	-		-	-	-	l	-		L				ш	LL.					თ	
n). <u>1</u> /	14	18	Cext1					ш.		-	-	-		-	-	-	-	-		=	-	-	ı	L		L				ш	ш			L	Open	Open	
or ope	13	17	ð							т				-	-	-	т	_	=	-	-	-	ł	OUL		НC	00							OUT		OUT	
TABLE III. Group A inspection for device type 01. itions (pins not designated may be high $\ge 2.0 \text{ V}$ , low $\le 0.7 \text{ V}$ , or open).	12	15	_ Q2					I.		_	ιT			-	c =	-	_	т		-	-	-						OUT	OUT			OUT					
Group A inspection for device type 01 designated may be high $\ge 2.0$ V, low $\le$	5	14	CLR2	5.5 V	5.5 V		,	8 =		A	В	в	4 <	τ (	n a	A	A	в	A	=	-	-			5.0 V	5.0 V		z	5.0 V			5.0 V	≥			E 0.V	5.0 V
<u>or devic</u> gh ≥ 2.0	10	13	B2	5.5 V	5.5 V			۲	а <	ζ =	=	в	e <	τ =	-	-	-	в	В	A	в	в			5.0 V	z		z	5.0 V			z	z			501	N N
ection for	თ	12	A2	5.5 V				A.	< □	o =	-			-	4	< 4	В	в	A	=	-	в	-			GND		GND	z			GND	GND				GND
A inspe ited ma	ω	10	GND	1	₽		-	GND		-	=				-	-	-	-		-	=	-	4	GND			-			-	-	=	-		= :		Π
<u>Group</u> designa	7	ი	Rext2 0	0	0	re omittec	omitted.	ц.			-			-		-	-	-		-	-	-	-		L 1	L		_	ш			ш	_			C,	<b>ა</b> თ
TABLE III. s (pins not o			Cext2 Re			ic tests ai	tests are				_							_			_		-		_	ш			ш			ш					
TAB ons (pii	9	ø				S°C and V	C and V <sub>IC</sub>			-	-		_	-	-	-	-	-	-	-	-	-	-				-						 				T OPEN
conditi	ى ك	2	Q2			$T_{c} = +125$	$1_{\rm C} = -55^{\circ}$			Т			- 3	-		-	Т			-	-	-	-	0		001	_				_		OUT			ē	OUT
Terminal cond	4	2	'õ			1, except	1, except	Ι.		-	Η				E =	-	-	Т	=	=	-	-	-				DUD			V OUT	V OUT					_	
Ĕ	ო	4	CLR1	5.5 V	5.5 \	ubgroup	dnoubdn	÷ ۵		٩	B	B	< <	< 0	ממ	ס ⊲	A	ш	A	-	-	-		5.0 V		201	o S Z			5.0 V	5.0 V		┢	N	$\vdash$	5.0 V	
	7	б	B1	5.5 V	5.5 V	ts as for s	ts as tor s	۲	<u> </u>	ζ =	-	ш	• • • • • • • • • • • • • • • • • • •	< =	-	-	-	ш	В	A	ю	ш	Γ <sub>c</sub> = -55°(	5.0 V		4	ĭZ			5.0 V	Z			N	5.0 V	Z	
	~	7	A1	5.5 V	ပ	, and limi	, and limi	٩	۵ ک	<u>-</u>	-			-	V	< ⊲	B	ш	A	-	-	ß	5°C and	Z			GND			Z	GND			GND	z	GND	
	Cases E, F	Case 2	Test no.	37	38	conditions	conditions	39	table = 40 A B = = = = = = = = = = = = = = = = = =	4	43	44	45	9 1	4/	49	50	51	52	53	54	55	Repeat subgroup 7 at $T_c = +125$ °C and $T_c = -55$ °C.	56	57	58	60 90	61	62	63	64	65	99	67	68	69	71
	-MIL-	STD-883 method -		3005	3005	s, terminal	s, terminal	3014		-	-			-	-	=	-	-	=	-	-	-	ogroup 7 a	3003	Fig. 3		-	-	-	-		-	-	-			=
		Symbol S n		CC2		ame tests	ame tests	Lruth	table	cical													epeat sut	tPLH1	_	tpLH2	t <sub>PLH3</sub>		t <sub>PHL1</sub>		t <sub>PHL2</sub>		t <sub>PHL3</sub>		t <sub>P(MIN)</sub>		
		Subgroup S		-	Tc = 25°C		S.	2	$Tc = 25^{\circ}C$																Tc = 25°C				1		<u> </u>		1		Ľ		

See footnotes at end of this table.

		Unit		Sti	=					
		ŝ	Max	6.0		-	-			
		Limits	Min	3.5	=	=	=			
		Measured terminal		Q2	Q2	ð	۵1 م			
	16	20	V <sub>cc</sub>	5.0 V						
	15 15	19	Rext1			_	_			
-  -  -	14	18	Cext1			_	_	to 75 ns		
or oper	13	17	۵۱			OUT	OUT	t <sub>PLH3</sub> is 5		
<u>11</u> . ≤ 0.7 V,	12	15	- Q2					to 74 ns;		
TABLE III. Group A inspection for device type 01. Terminal conditions (pins not designated may be high $\ge 2.0$ V, low $\le 0.7$ V, or open). <u>1</u>	11	14	CLR2	5.0 V	5.0 V			t <sub>PLH2</sub> is 5		
for devic igh ≥ 2.	10	13	B2	Z	5.0 V			to 57 ns;		
pection ay be h	თ	12	A2	GND	Z			t <sub>PLH1</sub> is 5		
up A insi inated m	8	10	GND	GND		=		follows:	i.25 µs.	
II. Grou ot desig	7	ი	Rext2	_	-			ts are as	s 3.0 to 6	
(pins n	9	ø	Cext2	_	-			and limi	and t <sub>P4</sub> i	°C
T Inditions	2	2	Q2	OUT	OUT			= +125°C	s 308 ns;	: T <sub>c</sub> = -55°C
ninal cc	4	5	ā1					cept T <sub>c</sub> =	s; t <sub>P(MIN)</sub> i	0, except
Terr	3	4	CLR1			5.0 V	5.0 V	oup 9, ex	5 to 48 n:	bgroup 1
	2	e	B1			5.0 V	N	as subgr	; t <sub>PHL3</sub> is !	as for su
	٢	2	A1			N	GND	nditions	to 92 ns	nditions
	Cases E, F	Case 2	Test no.	72	73	74	75	srminal cc	; t <sub>PHL2</sub> is 5	srminal cc
	-MIL-	Subgroup Symbol STD-883 method -		3003	Fig. 3			Same tests and terminal conditions as subgroup 9, except T <sub>c</sub> = +125°C and limits are as follows: t <sub>6LH1</sub> is 5 to 57 ns; t <sub>6LH2</sub> is 5 to 74 ns; t <sub>6LH3</sub> is 5 to 77 ns;	$t_{PHL1}$ is 5 to 75 ns; $t_{PHL2}$ is 5 to 92 ns; $t_{PHL3}$ is 5 to 48 ns; $t_{P(MN)}$ is 308 ns; and $t_{P4}$ is 3.0 to 6.25 $\mu$ s.	11 Same tests and terminal conditions as for subgroup 10, except T
		Symbol		t <sub>P4</sub>				Same te	t <sub>PHL1</sub> is {	Same te
		Subgroup		6	Tc = 25°C			10		11

NOTES:

- A.  $V_{IN} = 3.0 V$  minimum.
- B.  $V_{IN} = 0.0 V$  or GND.
- C. Apply input pulse

D. Test numbers 39 through 55 shall be run in sequence.

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E. Output voltages shall be either:

H > 1.5 V; L < 1.5 V

- F. Rext = 5 k $\Omega$  minimum to 180 k $\Omega$  maximum, connected to V<sub>cc</sub>; Cext  $\leq$  1,000 µF, connected to Rext terminal.
- G. Rext = 5 k $\Omega \pm 10\%$ , connected to V<sub>cc</sub>.
- 1. Rext = 10 kΩ ±10%, connect to  $V_{cc}$ ; Cext ≤ 1,000 µF ±10%, connected to Rext terminal.
- During subgroups 9, 10, 11 testing, Rext and Cext may remain applied on the side of the device not under test if desired. -;
- K. For circuit D, I<sub>L1</sub> limits are 120 mA to 360 mA.
- L. Rext = 10 kΩ  $\pm$ 10%, connect to V<sub>cc</sub>; Cext ≥ 45 pF connected to Rext terminal.

		Unit		>	=	-							-	-	-	=	μA	= :		-	-	-	=	-	-	-	-	-	=	-	-	=	=	=		-		-	-	=		-
		s	Max					0.4				-1.5	-		-	-	-340	-300	-400	-580	-300	-440	-680	-300	-340	-300	-400	-580	-300	-440	-680	-300	20			-		100	9 =	-		=
		Limits	Min	2.5	=	-	-										-100	-30	-160	-160	-30	-200	-200	-30	-100	-30	-160	-160	-30	-200	-200	-30					T	Ì	ĺ		T	
		Measured terminal		'a	a1	ā2	Q2	۰ م	a 1	Q2	02 02	A1	. B.	A2	B2	CLR2	A1	A1	A1	B1	B1	B1	CLR1	CLR1	A2	A2	A2	B2	B2	B2	CLR2	CLR2	A1	B1	CLR1	A2	B2 CI R2	A1	B1	CLR1	42 42	B2 CLR2
	16	20	V <sub>cc</sub>	4.5 V	-	-	-						-		-	-	5.5 V			-	=	-		-	-	-	=		=		-	-				-		-	-	-		-
	15	19	Rext1 See L		GND			UND															GND	GND																		
iU.c	<del>7</del>	18	Cext1 F See L 3		GND			UND	_														GND	GND													+					_
r open)	13	17	Q Q Q		4 mA G			4 mA	0														U	U								T					+	T		$\left  \right $	+	_
. 7 V,						hA		4			Υ.								_																		+			$\square$	+	_
, low ≤	12	15	2 Q2			/4 mA	~			-	/ 4 mA					A									,						0	0									_	
≥ 2.0 V	1	14	CLR2				2.0 V			2.0 V						-18 mA									4.5 V	=	-	-	=	-	GND	GND				_	GND 27V					5.5 V
be high	10	13	B2			0.7 V	2.0 V			0.7 V	2.0 V				-18 mA										4.5 V	-	-	0.4 V	=	-	4.5 V	4.5 V					2.7 V GND	5			1	o c.c
d may l	თ	12	A2			2.0 V	ပ			2.0 V	υ			-18 mA											0.4 V	-	-	GND	-	-	-	-				2.7 V	4.5 V 4.5 V	> ;			5.5 \	4.5 V
signate	ω	10	GND	GND	-	-	-						-	-	-	-	-			-	-	-	-	-	-	-	-	-	=	-	-	=		-		-		-	-	-		-
not de	7	ი	Rext2 See L				GND			1	GND																				GND	GND										
ns (pins	9	ω	Cext2 See L				GND				GND																				GND	GND										
onditio	5	7	Q2				4 mA			4 mA																																
Terminal con	4	ى	۵'	4 mA				4 m 4	t    t																																T	
	e	4	CLR1	2.0 V	2.0 V			2.0 <	× 0.7				10 ~ 1				4.5 V			-	=	-	GND	GND										GND	2.7 V				GND	5.5 V	T	
	0	ო	B1	0.7 V	2.0 V			0.7 \	× 0.7				-18 MA				4.5 V			0.4 V	=		4.5 V	4.5 V										2.7 V	GND				5.5 V	GND	T	
	~	5	A1	2.0 V	с			2.0 <	כ			-18 mA	~				0.4 V	= :		GND	-	-		-									2.7 V	4.5 V	4.5 V		╋	5.5 V	4.5 V		╋	
	Cases E, F	Case 2	Test no.	-	2	e	4		þ	7	ω		01	- 12	13	14		15 CKT B			6 CKT B	16CKT E. D	17 CKT A.C.D.E	7 CKT B	18 CKT A, C, D	8 CKT B	8 CKT E	19 CKT A, C	19 CKT B	19 CKT E. D	20 CKT A.C.D.E	0 CKT B				24	25 26				30	32 32
		STD-883 method -	<u> </u>	3006	-	-		3007					1			<u> </u>	3009			-	=	-	-	-	-	=	-		-		-	=	0	-				=	-	-		-
		Symbol S		V <sub>он</sub>				VoL				V <sub>IC</sub>					112																I <sub>H1</sub>					c i	Ž.			
		Subgroup S		-	Tc = 25°C							1					I																L					1				

TABLE III. Group A inspection for device type 02.

See footnotes at end of this table.

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		Unit		ШA	-	-	-	-	-	-	=	=						ЧF																	
		its	Max	-100	-130	-100	-130	-100	-130	-100	-130	11	27				See notes	A, B, D, E, and																	
		Limits	Min	-15	-30	-15	-30	-15	-30	-15	-30							Α, Ε																	
		Measured terminal		a1	6	_ Q2	ā2	Q2	Q2	a'	a' 1	Vcc	Vcc			AII	outputs	=	=	-		-		-		-	-	-	-		=	=	-	-	
	16	20	V <sub>cc</sub>	5.5 V	-	-	-	-	-	-	=	-	-			5.0 V	-	=	=	-	-	-		-	-	=	-	-	-	-	-	-	-	-	
	15	19	Rext1 See L	GND	GND											Ŀ		=	-	-	=	-		-	=	=	-	=	=	-		-	-	-	
U.d	4 4 14	18	Cext1 See L	GND	GND											ц		=	-	-	-	-		-	=	=	-	-	=	-		-	-	-	
or ope	13	17	ð	GND	GND											L	=	-	т	_	=	-	т.	_ =	-	т		=	=	-	=	=	-	-	
≤ 0.7 V	12	15	ā2			GND	GND									г	-	=	_	т	-	-	:	E =	=	-	-	-		т		-	-	-	
$2.0$ V, low $\leq 0.7$ V, or open).	11	14	CLR2			GND	GND	4.5 V	4.5 V			5.5 V	5.5 V			В	=	-	A	в	в	A	< 4	n =	=	=	-	A	A	в	A	-	-	-	
$\sim$	10	13	B2 (			GND	GND (	4.5 V 4	4.5 V 4			GND				A	В	A	=	-	в	ш	A :	=	=	=	-	-	=	в	В	A	В	в	
ay be h	6	12	A2			GND	GND	C 4	C 4			5.5 V G	C 5			A	A	в	=	-	-	-		<	۲ =	-	-	=	в	в	A	=	-	в	
nated m	ø	10	GND	GND	-	₽	-	-	-	-	-	2	-			GND		=	-	-	-	-		=	-	-	-	=	-	-		-	-	-	
ot design	7	ი	Rext2 ( See L					GND	GND					are omitted	e omitted.	F (		=	-	-	-	-		=	-	-	-	=	-	-		-	-	-	
(pins no	9	æ	Cext2 R See L S					GND	GND					25°C and V <sub>IC</sub> tests are omitted.	ic tests are	Ŀ		=	=	-	-	-		-	=	-	-	-	-	-		-	-	-	
nditions	£	7	02 S						O DND					25°C and	5°C and V	_	=	=	т	L	=	-	т.	_ =	=	-	-	-	т	_		=	-	-	
Terminal conditions (pins not designated may be high	4	5	a'					0		GND	GND			$PT_{C} = +1$	$= Dt T_c = -5$	г		=	_	г	=	-	:	c =	=		Т	=	=	-	=		=	=	
Tern	e S	4	CLR1	4.5 V	4.5 V					GND (	GND	5.5 V	5.5 V	oup 1, exc	oup 1, exc	в	=	=	A	В	в	A	< 4	0 0	0 4	< 4	В	=	-	-	A	-	-	-	
	2	ო	B1 (	4.5 V	4.5 V 4					GND	GND	GND		tor subgr	tor subgr	A	В	A	-	-	в	ш	4 -	-	=	=	-	=	=	в	В	A	В	в	-55°C.
	۲	2	A1	с 0	U U					GND	GND	5.5 V		nd limits as	nd limits as	A	A	в	=	-	-	-		<	< ⊲	< m	=	-	-	-	A	-	-	в	: and T <sub>c</sub> =
	Cases E, F	Case 2	Test no.	33 CKT A. B. D. E	CKT C	34 CKT A, B, D, E	CKT C	35 CKT A, B, D, E	35 CKT C	36 CKT A, B, D, E			38	Same tests, terminal conditions, and limits as for subgroup 1, except $T_{\rm C}$ = +1	Same tests, terminal conditions, and limits as for subgroup 1, except $T_c = -55^{\circ}C$ and $V_c$ tests are omitted	39	40	41	42	43	44	45	46	4/	40	50	51	52	53	54	55	56	57	58	Repeat subgroup 7 at $T_c = +125^{\circ}C$ and $T_c = -55^{\circ}C$ .
	MIL- C	STD-883 ( method -	ř	3011 33 A.	33	ب ج	34	Ř Ă	ಸ -	Ϋ́́	" 36	3005	3005	erminal col	erminal con	3014	_	_	_	-	=			_	=	-	-	_	=	-	_	-	-		oup 7 at T
	2			30								CC1 3(		ne tests, t	ne tests, t	Truth 3(	table	tests																	oeat subgi
		Subgroup Symbol		1	c = 25°C									2 San		7 Tr	Tc = 25°C tal																		8 Rep

TABLE III. <u>Group A inspection for device type 02</u> - Continued.

# MIL-M-38510/314C

See footnotes at end of this table.

		Unit		ns				-	=		-	-	-	=				-	-	=	-	-	=	-	-	-	-	=	-	-	-	-	-	-	-	=	-	-	-	ms =	:	-
		its	Max	75	75	60	09 20	70	05	85	85	20	70	60	60	۹ <i>۱</i>		-	=	=	-	-	=	160		-	-	=	-	-	=	775		-	=	-		-	-	8.0	:	-
		Limits	Min	5			-	-	-		-	-	-	-	= (	20		-	-	=	-	-	=	70	-	-	-	=	-	-	-	600		-	-	-		-	-	5.7	:	-
		Measured terminal		A1 to Q1	A2 to Q2	B2 to Q2				A2 to Q2	A1 to 01	B1 to 01	B2 to 02	CLR2 to Q2	CLR1 to Q1	5	a1	ō1	۵1 م	Q2	- Q2	02 02	Q2	Q2	02 02	_ Q2	Q2	۵1 م	°10	- 10	۵1 م	a1	'n	°1 10	6 b	Q2	02 02	02 02	Q2	07	ā2	°2 02
	16	20	V <sub>cc</sub>	5.0 V				-	-	:	-	-	-	-				-	=	=	-	-	=	-	-	-	-	=	-	-	-	-	-	-	-	-	-	-	-			-
	15	19	Rext1	ш		L	⊥z				F	Ŀ			z	<b>≺</b> =		-	=									ი		-	-		-	=	-							
4U.0 	<del>7</del>	18	Cext1	ш		L	r z				ш	ш			z	OPEN =		-	=									U		-	-	_		-	-							
or ope	13	17		OUT		Ŀ	INO		T						001				OUT					_				OUT			OUT	OUT			OUT							
Terminal conditions (pins not designated may be high $\ge 2.0$ V, low $\le 0.7$ V, or open).	12	15	ā2	$\left  \right $	┥			OUT	ΕC				OUT		╡						OUT	OUT			OUT	OUT		$\left  \right $			$\left  \right $						OUT	OUT		Ŀ	OUT	OUT
V, low	11	14	CLR2		5.0 V	> 0		Z	,				5.0 V 0	Z						5.0 V	-	-	=		-	-	-									5.0 V		-	=			=
h ≥ 2.0						+													-		٨	-7				٨	>											-		_		>
designated may be high $\geq 2.0^{\circ}$		13	B2		5.0 V	_		Ľ 0	u				⊻ 0	N N					-	5.0 V		Ľ 0	=	-			5.0 V										5.0 V	⊻ 0	-	_		5.0 V
ted may		12	0 A2		Z	2 S		GND	2	≤			GND	GND				-		Z	Z	GND	=	-	-	Z	Z									Z	Z	GND	-		:	Z
esignat	ω	10		GND			-	-	-		-	-	-	-				-	=	-	-	-	-	-	•	-	-	=	-	-	-	-	•	-	-	-	-	-	-			=
is not d	7	თ	Rext2		ц	L		z	L	L			ш	z						×	-	-	=	ი	-	-	-									-	-	-	-		:	-
nditions (pins not	9	∞	Cext2		шı	T		z	L	L			ш	z						OPEN	-	-	-	ი	-	-	-									-	-	-	-		:	-
conditi	2	2	Q2			00								OUT						OUT			OUT	OUT			OUT									OUT			OUT	OUT		
erminal	4	ى	٩'				OUT				OUT	OUT				Ę	2	OUT											OUT	OUT			OUT	OUT								
	ო	4	CLR1	5.0 V			≥0.6				5.0 V	5.0 V			Z	5.0 V												5.0 V	-	-	=	-	-	-	=							
	0	ო	B1	5.0 V			z∠				5.0 V	N			Z	5.0 <	<u>~</u>	Z	≥									5.0 V	5.0 V	N	=	-	-	5.0 V	5.0 V							
	-	2	A1	Z	Ţ		GND		T		Z	GND			GND	zz		GND	GND									Z	z	GND	-	-		Z	Z					T		
	Cases E, F	Case 2	Test no.	59	60	61	62	64	5E	ça	66	67	68	69	20	17	1	73	74	75	76	17	78	79	80	81	82	83	84	85	86	87	88	89	06	91	92	93	94	95 06	96	97
	MIL-	STD-883 method -	<u>I</u>	3003	Fig. 4 "			-	-			-		-				-	=	=	-	-	=	-		-	-	=	-	-	-	-		-	-	=	-	-	-			=
				tPLH1		tpLH2	t <sub>PLH3</sub>			Грнц1		t <sub>PHL2</sub>		t <sub>PHL3</sub>	+	tə,							_	t <sub>P2</sub>							_	t <sub>P3</sub>								t <sub>P5</sub>		
		Subgroup Symbol			$Tc = 25^{\circ}C$		<u> </u>		*					<u> </u>																												

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TABLE III. Group A inspection for device type 02 - Continued. nonditions (pins not designated may be high > 2.0 V. low < 0.7 V

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See notes at end of this table.

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		±									
		Unit		ms	=	-		=			
		Limits	Max	8.0	=	-		=			
		Lin	Min	5.7	=	-	-	-			
		Measured terminal		Q2	۵1	ā1	٩. מ	α1			
	16	20	V <sub>cc</sub>	5.0 V	=		=	=			
	15	19	Rext1		٦	-	-	-	us;		
en).	14 🗍 15	18	Cext1		٦	-	-	=	5 to 105		
V, or op	13	17	g		OUT			OUT	s; t <sub>PLH3</sub> is	i ms.	
low ≤ 0.7 V,	12	15	ā2						5 to 90 ns	5.5 to 8.5	
2.0 V, lo	11	14	CLR2	5.0 V					s; t <sub>P⊔H2</sub> is	and t <sub>P5</sub> is	
Terminal conditions (pins not designated may be high $\geq$ 2.0 V, low $\leq$ 0.7 V, or open).	10	13	B2	5.0 V					to 113 n	o 850 ns; a	
may be	6	12	A2	Z					t <sub>PLH1</sub> is 5	is 600 to	
ignated	8	10	GND	GND	=	-	-	=	follows:	95 ns; t <sub>P3</sub>	
not des	7	ი	Rext2	٦ ٦					ts are as	s 70 to 19	
ns (pins	9	8	Cext2	ſ					and limi	1 ns; t <sub>P2</sub> i	5°C
conditio	5	7	Q2	OUT					= +125°C	s 20 to 9′	t T <sub>c</sub> = -55
erminal	4	പ	'ą			OUT	OUT		kcept T <sub>c</sub> :	) ns; t <sub>P1</sub> i	0, excep
Ĕ	е	4	CLR1		5.0 V	-	=	=	oup 9, e;	is 5 to 9(	bgroup 1
	2	n	B1		5.0 V	5.0 V	z	Z	as subgr	ns; t <sub>PHL3</sub>	as for su
	-	2	A1		Z	Z	GND	GND	uditions	5 to 105	onditions
	Cases E, F	Case 2	Test no.	98	66	100	101	102	srminal cc	S; t <sub>PHL2</sub> iS	erminal cc
	-MIL-	Subgroup Symbol STD-883 method -	•	3003	Fig. 4	-	-		Same tests and terminal conditions as subgroup 9, except $T_c$ = +125°C and limits are as follows: teLH1 is 5 to 113 ns; teLH2 is 5 to 90 ns; teLH8 is 5 to 105 ns;	$t_{ m PH1}$ is 5 to 128 ns; $t_{ m PH2}$ is 5 to 105 ns; $t_{ m PH3}$ is 5 to 90 ns; $t_{ m P1}$ is 20 to 91 ns; $t_{ m 22}$ is 70 to 195 ns; $t_{ m 23}$ is 600 to 850 ns; and $t_{ m 25}$ is 5.5 to 8.5 ms.	Same tests and terminal conditions as for subgroup 10, except $T_c$ = -55°C
		Symbol		tp5					Same te	t <sub>PHL1</sub> is	Same te
		Subgroup		6	Tc = 25°C				10		11
		•		-	-						

TABLE III. Group A inspection for device type 02 - Continued.

NOTES:

A.  $V_{IN} = 3.0 V$  minimum.

B.  $V_{IN} = 0.0 V$  or GND.

C. Apply input pulse

\_\_\_\_\_\_\_ - - - - 2.5 V min/5.5 V max.

D. Test numbers 39 through 58 shall be run in sequence.

E. Output voltages shall be either:

H > 1.5 V; L < 1.5 V

Rext = 1.4 kΩ minimum to 70 kΩ maximum, connected to  $V_{cc}$ ; Cext  $\leq$  1,000 µF, connected to Rext terminal. Ŀ.

G. Rext = 2 k $\Omega \pm 10\%$ , connected to V<sub>cc</sub>; Cext = 80 pF  $\pm 10\%$ , connected to Rext terminal.

1. Rext = 10 kΩ ±10%, connect to  $V_{cc}$ ; Cext = 100 pF ±10%, connected to Rext terminal.

J. Rext = 10 kΩ ±10%, connect to  $V_{cc}$ ; Cext = 1.0 µF ±10%, connected to Rext terminal.

K. Rext = 2 k $\Omega \pm 10\%$ , connect to V<sub>cc</sub>.

L. Note F may apply during subgroups 1, 2, and 3 testing if desired.

M. During subgroups 9, 10, 11 testing, Rext and Cext may remain applied on the side of the device not under test if desired.

N. Rext = 10 kΩ  $\pm$ 10%, connect to V<sub>cc</sub>; Cext ≥ 45 pF connected to Rext terminal.

		Unit		V	=	-	=	-	-	=		V	5. =	=	=	=	=	-			=	=	=	=	=	шA	=	=	=	=	-				œ						
		its	Max			0.4	0.4	-1.5	=	=		-400	2 =	=	=	=	20	=		: :	100	2 =	=	=	=	-100	-130	-100	-130	11	11				See notes A,						
		Limits	Min	2.5	2.5							-160	2 =	-	-	=										-15	-30	-15	-30						Sec						
		Measured terminal		Ø	ıØ	ø	١Ø	A1	A2	B1	B2 OLD	0LR ∆1	A2	B1	B2	CLR	A1	A2	B1	B2 OLD	2LK	- V	81 12	B2	CLR	Ø	ø	ıØ	١Ø	Vcc	V <sub>cc</sub>			AII	outputs		-				
	14	20	V <sub>cc</sub>	4.5 V	-	-	-	-	=			551		=	=	=	-	-			=	=	=	=	=	=	=	-	-	=	=			5.0 V	-		= :				:
	13	19	<u>Rext</u> Cext (see I)	GND			GND																			GND	GND							×,	-		-				:
u.U.	12 10	18	NC																																						
Terminal conditions (pins not designated may be high $\ge 2.0$ V, low $\le 0.7$ V, or open).	11	16	Cext (see I)									Ì	Ì																					×	-		-				:
ow ≤ 0.7	10	14	NC																																						_
≥ 2.0 V, I	6	13	Rint	GND	4.5 V	4.5 V	GND					Ì	l													GND	GND	4.5 V	4.5 V	5.5 V	5.5 V				_	T		T		T	_
be high	ω	12	σ	4 mA		4 mA						l														GND	GND								-	= :	I.	_	т.		-
ted may	7	10	GND	GND	=	=	-	=	=	=		-	=	=	=	=	=	=			=	=	=	=	=	=	-	-	-	=	=	re omitted	e omitted	GND			-				:
designat	9	6	ō		4 mA		4 mA																					GND	GND			∕ <sub>1 C</sub> tests a	= -55°C and V <sub>1C</sub> tests are omitted.	т		= .	:	т.		т :	г
pins not	5	∞	CLR	2.0 V	=	=	-				4 - C 7	- IØ IIIA				0.4 V					Z. / V				5.5 V	4.5 V	-	-	-	5.5 V	5.5 V	5°C and V	°C and V	ш	ш	A ·	A	ш·	< 0	л <	A
nditions (	4	9	B2	٦ ٦	0.7 V	0.7 V	٦				-18 mA			4.5 V	0.4 V				GND	2.7 V			GND	5.5 V		-	۔ ٦	GND	GND	GND	5.5 V	ot $T_c = 12!$	ot $T_c = -55$	ш	ш	A	= :				:
ninal cor	ю	4	B1	2.0 V			2.0 V			-18 mA				0.4 V	4.5 V				2.7 V	GND			55V	GND	)	4.5 V	4.5 V			GND	5.5 V	o 1, excep	o 1, excep	ю	B	A	= :		= (	ш	n
Terr	2	ო	A2						-18 mA			4 5 V	0.4 V				GND	2.7 V				ערא ערא ע	> 0.0							5.5 V	٦	subgroup	subgroup	В	A	4	B		= ‹	₹ -	
	~	5	A1	0.7 V			0.7 V	-18 mA				04 \	4.5 V				2.7 V	GND			<b>к</b> 2		GIA			GND	GND			5.5 V	٦	d limits as	d limits as	ш	A	4	B				:
	Case A,B,C,D	Case 2	Test no.	-	2	ю	4		9	7	ω 0	40 10	1 5	12	13	14	15	16	17	18	61	21	20	23	24	25 CKT A.D	25 CKT C	26 CKT A.D	26 CKT C	27	28	Same tests, terminal conditions, and limits as subgroup 1, except $T_c$ = 125°C and $V_{1c}$ tests are omitted	Same tests, terminal conditions, and limits as subgroup 1, except $\ensuremath{T_{C}}$	29	29A	30	31	321	33	85 Y	cs
	MIL-STD-	883 method	<u> </u>	3006	3006	3007	3007		1		[	3000	8	=	=	=	3010				=	-	=	=	=	3011	=	=	-	3005	3005	terminal col	terminal col	3014							_
	M	Symbol r		V <sub>OH</sub>		VoL		Vic				_	see	note C			IH1					ZHI				los				lcc1	lcc2	ime tests, t	ime tests, t	Truth	able	test					-
		Subgroup Sy			Tc = 25°C									č												<u> </u>							3 Sa		$Tc = 25^{\circ}C$ t						

TABLE III. Group A inspection for device type 03.

See footnotes at end of this table.

# MIL-M-38510/314C

		Unit			~										su	-	-	-	=	-	-	sti				
			Max		See notes A, B										50	61	32	38	49	50	205	6.0				
		Limits	Min		See no										5	•		.,	7	4,	2	3.5 6				
		Measured terminal	-		outs										A1 to ¯	10	to Q	٥Q	٥Q	to Ō	~	ø				
		Measure		AII	outputs	-	-	-	-	-	-	-	-	-		B1 to $\bar{\mathrm{Q}}$	CLR to Q	A1t	B1 to Q	CLR to	0	0	ns;			
	14	20	V <sub>CC</sub>	5.0 V	-	-	=	-	-	-	=	=	-		5.0 V	-	-	=		=	=	-	s 5 to 57			
et4U.o	-13 13	19	Rext Cext (see I)	Y	=	=	=	=	=	-	=	=	=		×	×	Σ	ч	х	Σ	ს	z	IS; t <sub>PLH1</sub> i			
	12	18	NC																				s 5 to 48 r			
id. ' V, or op	11	16	Cext (see I)	×	-	-	-	-	-	-	=	=	-		×	×	Σ	¥	х	Σ		ш	ns; t <sub>PHL3</sub> is			
Continue low ≤ 0.7	10	14	S																				is 5 to 92			
Terminal conditions (pins not designated may be high $\ge 2.0$ V, low $\le 0.7$ V, or open).	6	13	Rint																				-125°C and limits are as follows: t <sub>PHL1</sub> is 50 to 75 ns; t <sub>PHL2</sub> is 5 to 92 ns; t <sub>PHL3</sub> is 5 to 48 ns; t <sub>PLH1</sub> is 5 to 57 ns;			
<u>device ty</u> be high	ω	12	ø	т	_	_	т			I	_		т				OUT	OUT	OUT		OUT	OUT	is 50 to 7!			
ction for a	2	10	GND	GND	=	-	=	=	=	-	=	=	-		GND	-	-			=	=	=	DWS: t <sub>PHL1</sub>			
<u>A inspec</u> designa	9	6	١Q	-	т	т	L	н	н	L	т	т	-		OUT	OUT				OUT			re as follc			
. <u>Group</u> (pins not	5	8	CLR	A	В	A	A	В	A	A	В	A	A		5.0 V	5.0 V	N	5.0 V	5.0 V	N	5.0 V		nd limits a	5 μs.		
ABLE III nditions	4	9	B2	A	в	В	A		=		=	=	=		5.0 V	5.0 V	N	5.0 V	5.0 V	Z	5.0 V	5.0 V	+125°C aı	3.0 to 6.2	: -55°C.	
T minal co	ю	4	B	A	-	=	=	=	-	-	=	=	=		5.0 V	≧	5.0 V	5.0 V	N	5.0 V	5.0 V	Z	ept T <sub>c</sub> = -	and t <sub>P4</sub> is :	cept T <sub>c</sub> =	
Ter	2	ю	A2	A	=	=	=	-	=	=	=	=	в	= -55° C.	5.0 V	GND	GND	5.0 V	GND	GND	5.0 V	GND	oup 9 exc	: 308 ns; a	oup 10 ex	
	-	5	A1	В	=	=	=	A	A	в	A	=	=	C and T <sub>c</sub> =	z	GND	GND	N	GND	GND	Z	GND	s as subgr	IS; t <sub>P(MIN)</sub> is	s as subgr	
	Case A,B,C,D	Case 2	Test no.	36	37	38	39	40	41	42	43	44	45	c = +125° (	46	47	48	49	50	51	52	53	l conditions	is 5 to 75 n	I conditions	
	MIL-STD-	883 method		3014	=	-	=	=	=	=	=	=	=	Repeat subgroup 7 at $T_c$ = +125° C and $T_c$ = -55° C	3003	(Fig. 3)	=	-	-	=	=	=	Same tests and terminal conditions as subgroup 9 except $T_{\rm C}$ = +	$t_{PLH2}$ is 5 to 74 ns; $t_{PLH3}$ is 5 to 75 ns; $t_{P(MIN)}$ is 308 ns; and $t_{P4}$ is 3.0 to 6.25 µs.	Same tests and terminal conditions as subgroup 10 except $T_{\rm C}$ =	
	Σ	Symbol		Truth	table	test								epeat subc	t <sub>PHL1</sub>	t <sub>PHL2</sub> (	t <sub>PHL3</sub>	t <sub>PLH1</sub>	t <sub>PLH2</sub>	t <sub>PLH3</sub>	t <sub>P(MIN)</sub>	t <sub>P4</sub>	ame tests	PLH2 IS 5 to	ame tests	
		Subgroup S		7	Tc = 25°C									8	+	Tc = 25°C	<u> </u>			<u> </u>	<u> </u>	<u> </u>	10 S	t	11 S	NOTES

 $V_{IN} = 3.0 V minimum.$ 

 $V_{IN} = 0.0 V$  or GND. i п. с. п. п.

For circuit D, IIL1 limits are 120 to 360 mA. Test numbers 29 through 45 shall be run in sequence.

Output voltages shall be either:

H > 1.5 V; L < 1.5 V Cext connected to Rext/Cext through a 1,000 pF  $\pm 10\%$  capacitor.

Rext/Cext connected to Vcc through a 5  $k\Omega\pm10\%$  resistor. Note K may apply during subgroups 1, 2, and 3 testing if desired. ட் ப் \_ – –

- - - 2.5 V min/5.5 V max. --- 0 V Apply input pulse

Rext/Cext connected to  $V_{cc}$  through a 5 kΩ to 180 kΩ resistor, and Cext connected to Rext/Cext through a ≤ 1,000 µF capacitor.

Cext connected to Rext/Cext through A  $\ge$  45 pF capacitor, Rext/Cext connected to V<sub>cc</sub> through a 10 kΩ  $\pm$ 10% resistor. Rext/Cext connected to V<sub>cc</sub> through a 10 kΩ  $\pm$ 10% resistor. żΞż

## 5. PACKAGING

5.1 <u>Packaging requirements.</u> For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When actual packaging of materiel is to be performed by DoD personnel, these personnel need to contact the responsible packaging activity to ascertain requisite packaging requirements. Packaging requirements are maintained by the Inventory Control Point's packaging activity within the Military Department of Defense Agency, or within the Military Department's System Command. Packaging data retrieval is available from the managing Military Department's or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

# 6. NOTES

(This section contains information of a general or explanatory nature which may be helpful, but is not mandatory.)

6.1 <u>Intended use.</u> Microcircuits conforming to this specification are intended for original equipment design applications and logistic support of existing equipment.

- 6.2 Acquisition requirements. Acquisition documents should specify the following:
  - a. Title, number, and date of the specification.
  - b. Complete part number (see 1.2).
  - c. Requirements for delivery of one copy of the quality conformance inspection data pertinent to the device inspection lot to be supplied with each shipment by the device manufacturer, if applicable.
  - d. Requirements for certificate of compliance, if applicable.
  - e. Requirements for notification of change of product or process to contracting activity in addition to notification to the qualifying activity, if applicable.
  - f. Requirements for failure analysis (including required test condition of method 5003 of MIL-STD-883), corrective action, and reporting of results, if applicable.
  - g. Requirements for product assurance options.
  - h. Requirements for special carriers, lead lengths, or lead forming, if applicable. These requirements should not affect the part number. Unless otherwise specified, these requirements will not apply to direct purchase by or direct shipment to the Government.
  - j. Requirements for "JAN" marking.

6.3 <u>Superseding information</u>. The requirements of MIL-M-38510 have been superseded to take advantage of the available Qualified Manufacturer Listing (QML) system provided by MIL-PRF-38535. Previous references to MIL-M-38510 in this document have been replaced by appropriate references to MIL-PRF-38535. All technical requirements now consist of this specification and MIL-PRF-38535. The MIL-M-38510 specification sheet number and PIN have been retained to avoid adversely impacting existing government logistics systems and contractor's parts lists.

6.4 <u>Qualification</u>. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturers List QML-38535 whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or purchase orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from DSCC-VQ, 3990 E. Broad Street, Columbus, Ohio 43123-1199.

6.5 <u>Abbreviations, symbols, and definitions.</u> The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535, MIL-HDBK-1331, and as follows:

GND	Ground zero voltage potential
I <sub>IN</sub>	Current flowing into an input terminal
V <sub>IC</sub>	Input clamp voltage
V <sub>IN</sub>	Voltage level at an input terminal

6.6 <u>Logistic support.</u> Lead materials and finishes (see 3.4) are interchangeable. Unless otherwise specified, microcircuits acquired for Government logistic support will be acquired to device class B (see 1.2.2), lead material and finish A (see 3.4). Longer length leads and lead forming should not affect the part number.

6.7 <u>Substitutability.</u> The cross-reference information below is presented for the convenience of users. Microcircuits covered by this specification will functionally replace the listed generic-industry type. Generic-industry microcircuit types may not have equivalent operational performance characteristics across military temperature ranges or reliability factors equivalent to MIL-M-38510 device types and may have slight physical variations in relation to case size. The presence of this information should not be deemed as permitting substitution of generic-industry types for MIL-M-38510 types or as a waiver of any of the provisions of MIL-PRF-38535.

Military device	Generic-industry
type	type
01	54LS123, 74LS123
02	54LS221, 74LS221
03	54LS122, 74LS122

6.8 <u>Manufacturers' designation</u>. Manufacturers' circuits, which form a part of this specification, are designated as shown in table IV herein.

		M	anufacturers		
	А	В	С	D	E
Device	Texas Instru-	Signetics	National	Motorola	Raytheon
type	ments Inc.	Corporation	Semiconductor Corp	Inc	Company
01	Х		X	Х	
02	Х	Х	Х	Х	
03	X		X	X	X

#### TABLE IV. Manufacturers' designation.

6.9 <u>Changes from previous issue.</u> Asterisks are not used in this revision to identify changes with respect to the previous issue due to the extensiveness of the changes.

Custodians: Army - CR Navy - EC Air Force - 11 DLA - CC

Review activities: Army - MI, SM Navy - AS, CG, MC, SH, TD Air Force - 03, 19, 99 Preparing activity: DLA - CC

(Project 5962-1964)

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	INSTRUCTIONS	numeric number and sudday latter standakers'
		cument number and revision letter should be given.
2. The submitter of this form must complete b	blocks 4, 5, 6, and 7, and send to prepar	ing activity.
3. The preparing activity must provide a reply	within 30 days from receipt of the form.	
		aivers, or clarification of requirements on current con y portion of the referenced document(s) or to amend
I RECOMMEND A CHANGE:	1. DOCUMENT NUMBER MIL-M-38510/314C	2. DOCUMENT DATE (YYYYMMDD) 2003-07-14
3. DOCUMENT TITLE heet/MICROCIRCUITS, DIGITAL, LOW-PO	WER SCHOTTKY TTL, MONOSTA	BLE MULTIVIBRATORS, MONOLITHIC SILIC
4. NATURE OF CHANGE (Identify paragraph I	number and include proposed rewrite, if	possible. Attach extra sheets as needed.)
5. REASON FOR RECOMMENDATION		
6. SUBMITTER		N
a. NAME (Last, First Middle Initial)	b. ORGANIZATIO	
		DN (Include Area Code) 7. DATE SUBMITTED (YYYYMMDD)
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<ul> <li>a. NAME (Last, First Middle Initial)</li> <li>c. ADDRESS (Include Zip Code)</li> <li>8. PREPARING ACTIVITY</li> <li>a. NAME Defense Supply Center, Columbus</li> <li>c. ADDRESS (Include Zip Code)</li> </ul>	d. TELEPHONE (1) Commercial (2) DSN ( <i>If applicable</i> ) b. TELEPHONE (1) Commercial IF YOU DO NOT	(Include Area Code) (Include Area Code 614-692-0536 RECEIVE A REPLY WITHIN 45 DAYS, CONTACT:
<ul> <li>a. NAME (Last, First Middle Initial)</li> <li>c. ADDRESS (Include Zip Code)</li> <li>8. PREPARING ACTIVITY</li> <li>a. NAME Defense Supply Center, Columbus</li> </ul>	d. TELEPHONE (1) Commercial (2) DSN ( <i>If applicable</i> ) b. TELEPHONE (1) Commercial IF YOU DO NOT Defense Stand 8725 John J. K Fort Belvoir, Vi	(Include Area Code) (Include Area Code (Include Area Code 614-692-0536 (2) DSN 850-0536